

MC33039, NCV33039

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
V _{CC} Zener Current	I _Z (V _{CC})	30	mA
Logic Input Current (Pins 1, 2, 3)	I _{IH}	5.0	mA
Output Current (Pins 4, 5), Sink or Source	I _{DRV}	20	mA
Power Dissipation and Thermal Characteristics			
Maximum Power Dissipation @ T _A = +85°C	P _D	650	mW
Thermal Resistance, Junction-to-Air	R _{θJA}	100	°C/W
Operating Junction Temperature	T _J	+150	°C
Operating Ambient Temperature Range	T _A	-40 to +85	°C
MC33039		-40 to +125	
NCV33039			
Storage Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS (V_{CC} = 6.25 V, R_T = 10 k, C_T = 22 nF, T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
LOGIC INPUTS					
Input Threshold Voltage					V
High State	V _{IH}	2.4	2.1	–	
Low State	V _{IL}	–	1.4	1.0	
Hysteresis	V _H	0.4	0.7	0.9	
Input Current	I _{IH}				μA
High State (V _{IH} = 5.0 V)					
φ _A		– 40	– 60	– 80	
φ _B , φ _C		–	– 0.3	– 5.0	
Low State (V _{IL} = 0 V)	I _{IL}				
φ _A		– 190	– 300	– 380	
φ _B , φ _C		–	– 0.3	– 5.0	

MONOSTABLE AND OUTPUT SECTIONS

Output Voltage	V _{OH}				V
High State					
f _{out} (I _{source} = 5.0 mA)		3.60	3.95	4.20	
φ _A (I _{source} = 2.0 mA)		4.20	4.75	–	
Low State	V _{OL}				
f _{out} (I _{sink} = 10 mA)		–	0.25	0.50	
φ _A (I _{sink} = 10 mA)		–	0.25	0.50	
Capacitor C _T Discharge Current	I _{dischg}	20	35	60	mA
Output Pulse Width (Pin 5)	t _{PW}	205	225	245	μs

POWER SUPPLY SECTION

Power Supply Operating Voltage Range	V _{CC}	5.5	–	V _Z	V
MC33039 (T _A = –40° to +85°C)					
NCV33039 (T _A = –40° to +125°C)					
Power Supply Current	I _{CC}	1.8	3.9	5.0	mA
Zener Voltage (I _Z = 10 mA)	V _Z	7.5	8.25	9.0	V
Zener Dynamic Impedance (ΔI _Z = 10 mA to 20 mA, f ≤ 1.0 kHz)	Z _{ka}	–	2.0	5.0	Ω

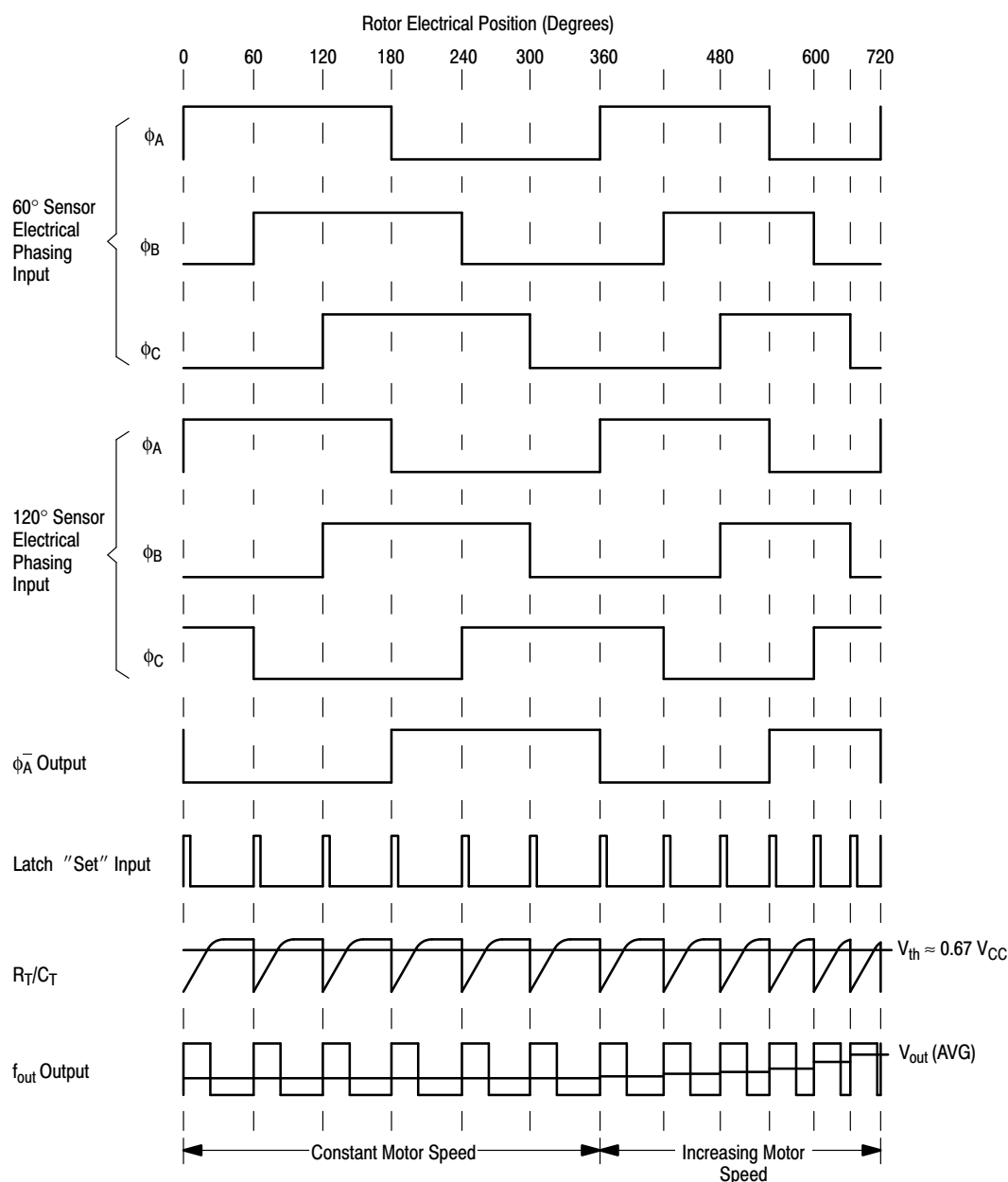


Figure 1. Typical Three Phase, Six Step Motor Application

OPERATING DESCRIPTION

The MC33039 provides an economical method of implementing closed-loop speed control of brushless DC motors by eliminating the need for a magnetic or optical tachometer. Shown in the timing diagram of Figure 1, the three inputs (Pins 1, 2, 3) monitor the brushless motor rotor position sensors. Each sensor signal transition is digitally detected, OR'ed at the Latch 'Set' Input, and causes C_T to discharge. A corresponding output pulse is generated at f_{out} (Pin 5) of a defined amplitude, and programmable width determined by the values selected for R_T and C_T (Pin 6). The average voltage of the output pulse train increases with motor speed. When fed through a low pass filter or integrator, a DC voltage proportional to speed is generated. Figure 2 shows the proper connections for a typical closed

loop application using the MC33035 brushless motor controller. Constant speed operation down to 100 RPM is possible with economical three phase four pole motors.

The ϕ_A inverter output (Pin 4) is used in systems where the controller and motor sensor phasing conventions are not compatible. A method of converting from either convention to the other is shown in Figure 3. For a more detailed explanation of this subject, refer to the text above Figure 39 on the MC33035 data sheet.

The output pulse amplitude V_{OH} is constant with temperature and controlled by the supply voltage on V_{CC} (Pin 8). Operation down to 5.5 V is guaranteed over temperature. For systems without a regulated power supply, an internal 8.25 V shunt regulator is provided.

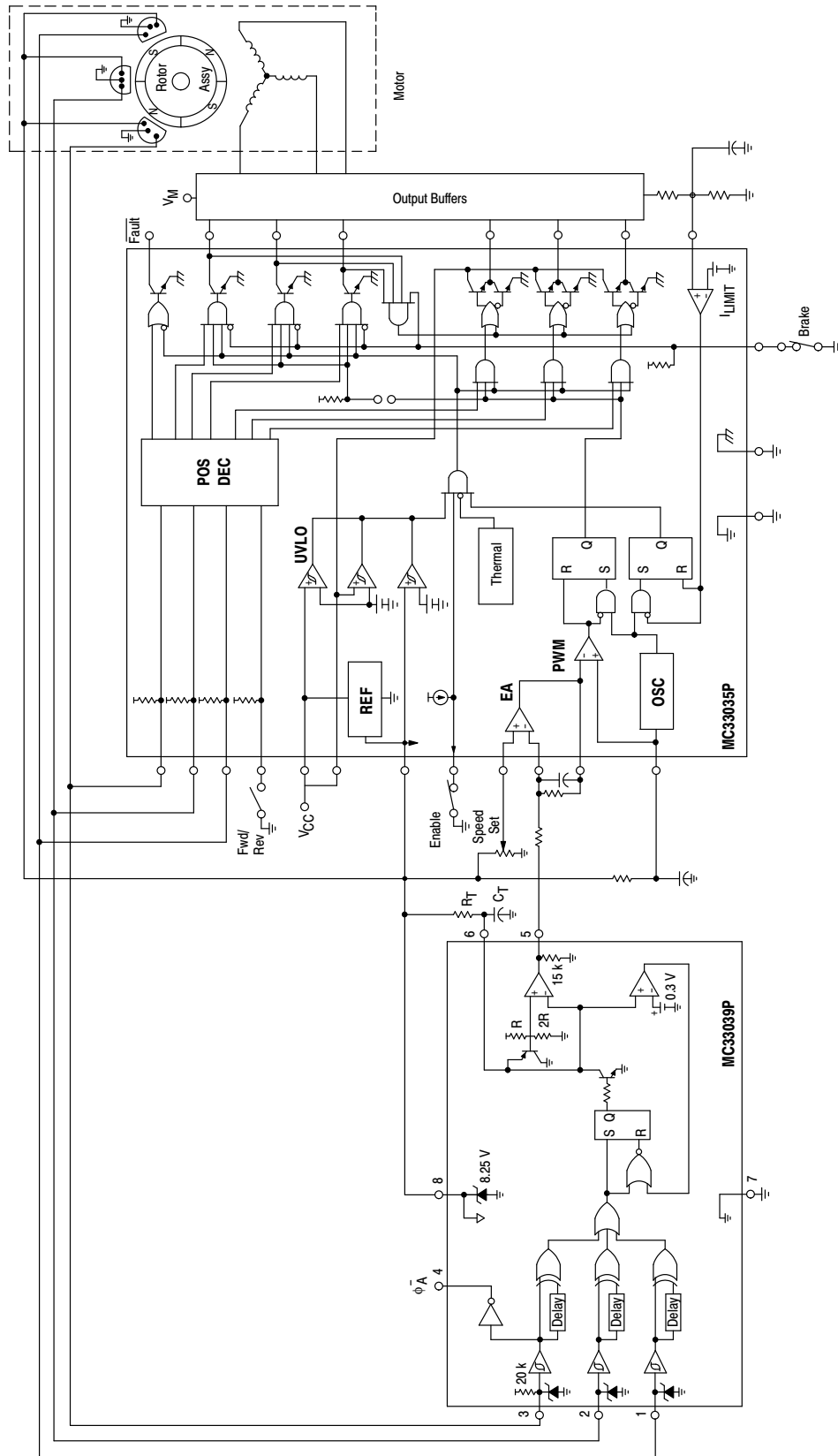


Figure 2. Typical Closed Loop Speed Control Application

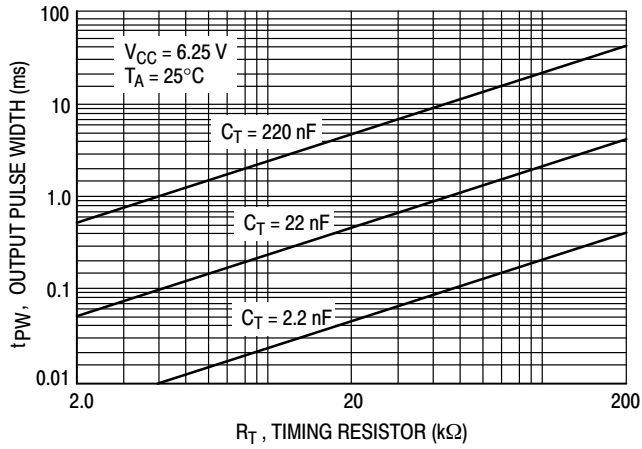


Figure 3. f_{out} , Pulse Width versus Timing Resistor

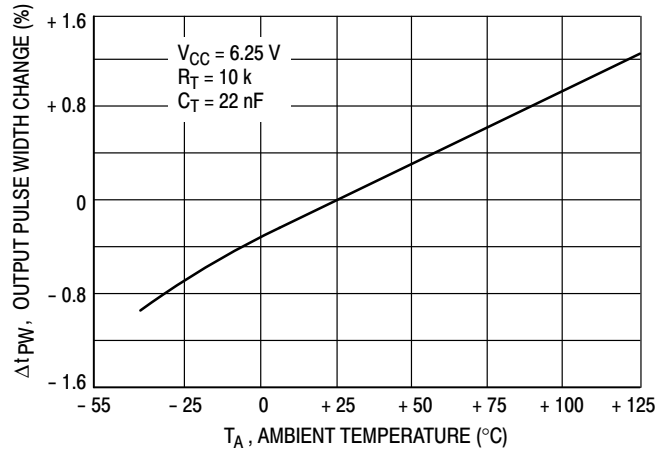


Figure 4. f_{out} , Pulse Width Change versus Temperature

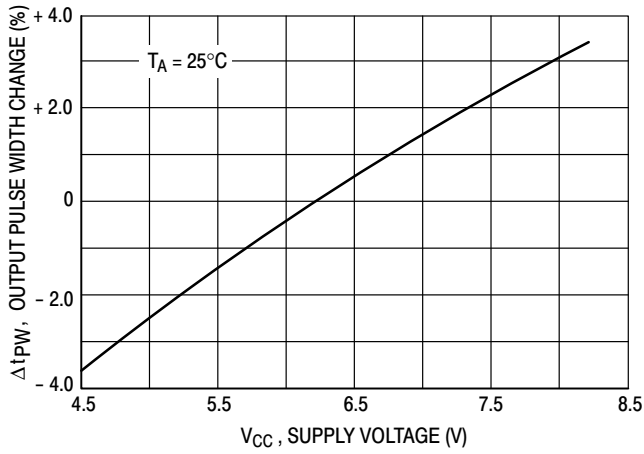


Figure 5. f_{out} , Pulse Width Change versus Supply Voltage

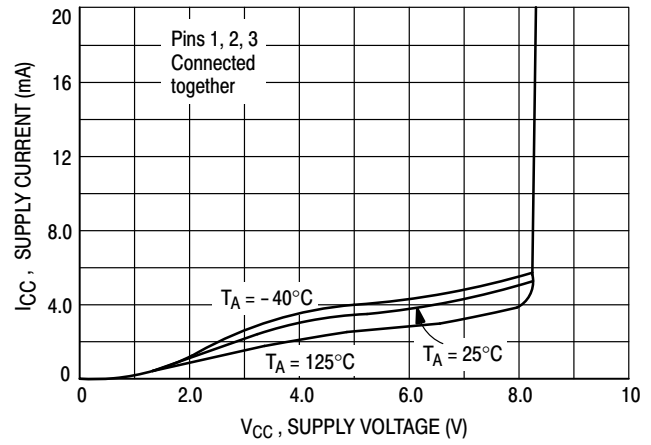


Figure 6. Supply Current versus Supply Voltage

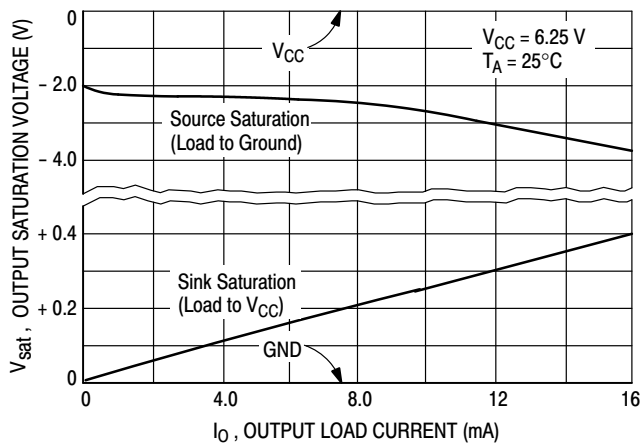


Figure 7. f_{out} , Saturation versus Load Current

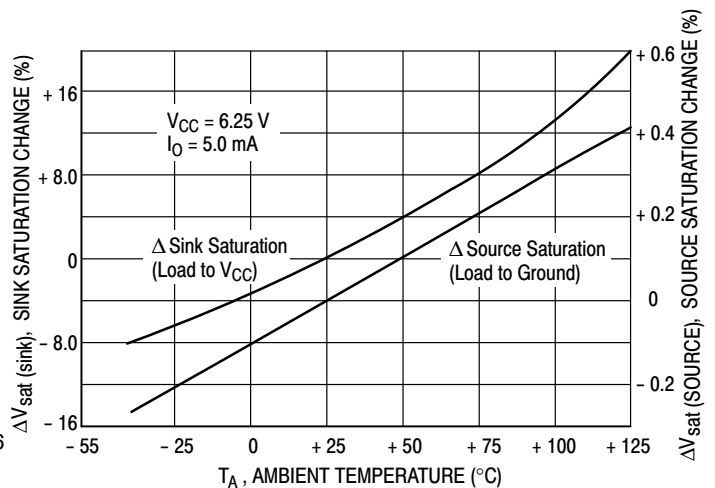


Figure 8. f_{out} , Saturation Change versus Temperature

MC33039, NCV33039

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping [†]
MC33039D	$T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	SOIC-8	98 Units / Rail
MC33039DG			2500 / Tape & Reel
MC33039DR2			
MC33039DR2G			
MC33039P		PDIP-8	50 Units / Rail
MC33039PG			
NCV33039DR2*	$T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	SOIC-8	2500 / Tape & Reel
NCV33039DR2G*			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV33039: $T_{\text{low}} = -40^{\circ}\text{C}$, $T_{\text{high}} = +125^{\circ}\text{C}$. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

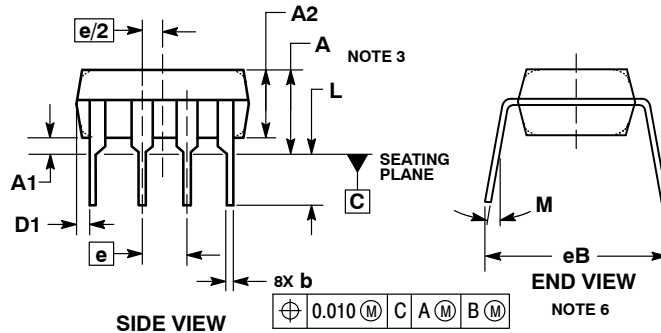
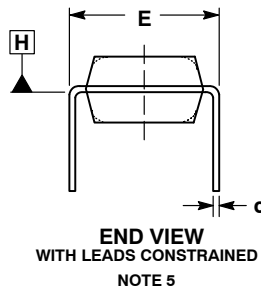
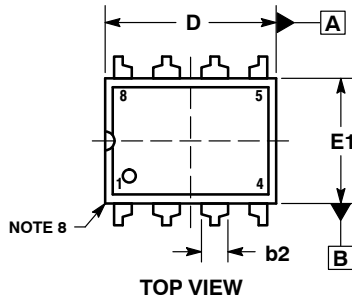
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SCALE 1:1

PDIP-8
CASE 626-05
ISSUE P

DATE 22 APR 2015

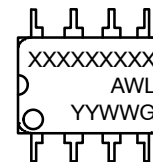


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	---	0.210	---	5.33
A1	0.015	---	0.38	---
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005	---	0.13	---
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	---	0.430	---	10.92
L	0.115	0.150	2.92	3.81
M	---	10°	---	10°

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

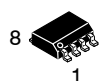
STYLE 1:

- PIN 1: AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. V_{CC}

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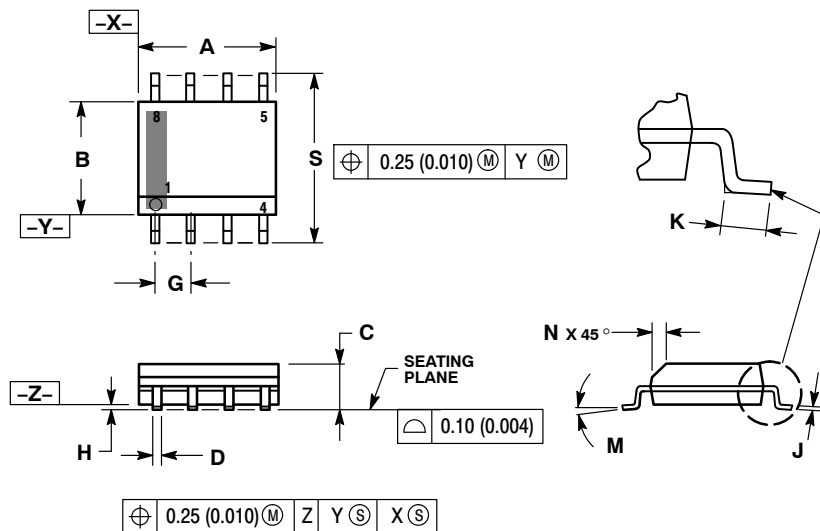
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

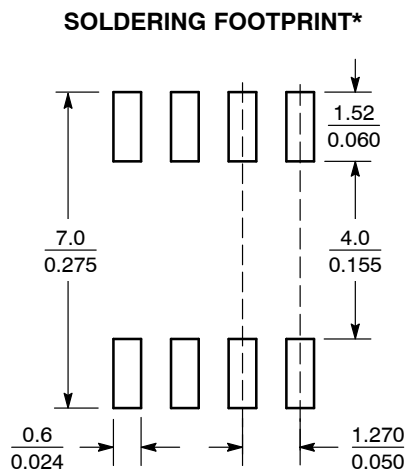


NOTES:

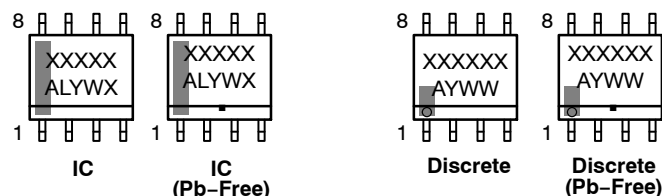
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC MARKING DIAGRAM*



SCALE 6:1 (mm/inches)



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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